

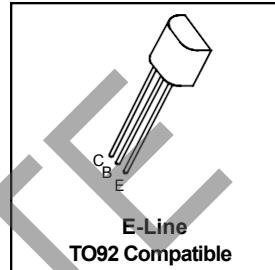
NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

ZTX449

ISSUE3

FEATURES

- * 30 Volt V_{CEO}
- * 1 Amp continuous current
- * $P_{tot} = 1$ Watt



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	1	A
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

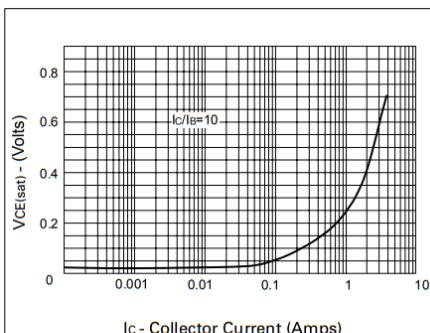
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50			V	$I_C=100\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	$I_C=10\text{mA}, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}, I_C=0$
Collector Cut-Off Current	I_{CBO}			0.1 10	μA	$V_{CB}=40\text{V}$ $V_{CB}=40\text{V}, T_{amb}=100^\circ\text{C}$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=4\text{V}, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5 1	V	$I_C=1\text{A}, I_B=100\text{mA}^*$ $I_C=2\text{A}, I_B=200\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.25	V	$I_C=1\text{A}, I_B=100\text{mA}^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$			1	V	$I_C=1\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	F_E	0 100 80 40		300		$I_C=50\text{mA}, V_{CE}=2\text{V}^*$ $I_C=500\text{mA}, V_{CE}=2\text{V}^*$ $I_C=1\text{A}, V_{CE}=2\text{V}^*$ $I_C=2\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T	150			MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=100\text{MHz}$
Output Capacitance	C_{obo}			15	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$

*Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$

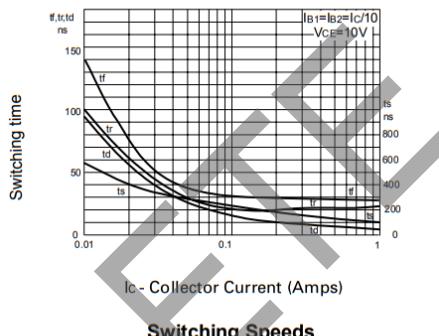
ZTX449

TYPICAL CHARACTERISTICS

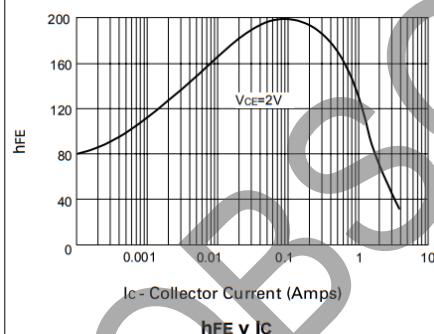
OBSOLETE - PART DISCONTINUED



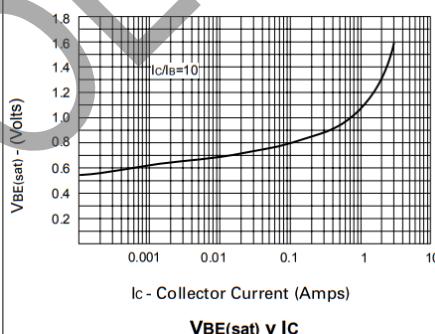
$V_{CE(sat)}$ v I_C



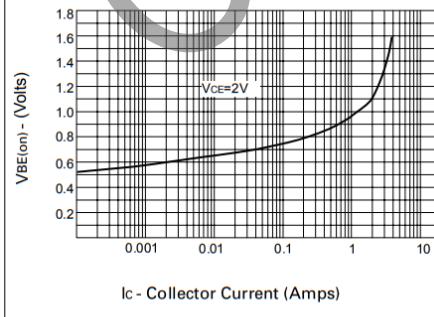
Switching Speeds



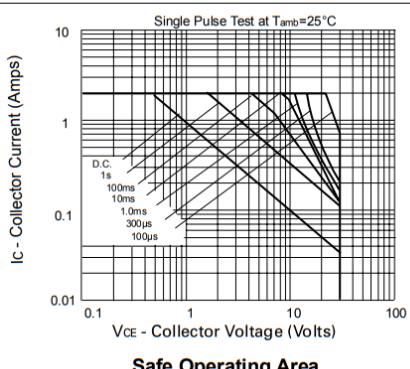
hFE v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area